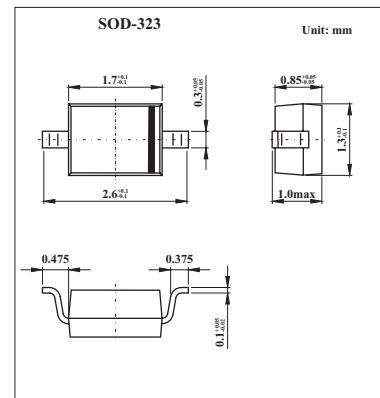


General purpose PIN diode

BAP51-03

■ Features

- Low diode capacitance
- Low diode forward resistance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Min	Max	Unit
continuous reverse voltage	VR		50	V
continuous forward current	IF		50	mA
total power dissipation Ts = 90°C	Ptot		500	mW
storage temperature	Tstg	-65	+150	°C
junction temperature	Tj	-65	+150	°C
thermal resistance from junction to soldering point	Rth j-s		120	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
forward voltage	VF	IF = 50 mA		0.95	1.1	V
reverse voltage	VR	IR = 10 μA	50			V
reverse current	IR	VR = 50 V			100	nA
diode capacitance	Cd	VR = 0; f = 1 MHz		0.4		pF
		VR = 1V; f = 1 MHz		0.3	0.55	
		VR = 5V; f = 1 MHz		0.2	0.35	
diode forward resistance	RD	IF = 0.5 mA; f = 100 MHz; note 1		5.5	40	Ω
		IF = 1 mA; f = 100 MHz; note 1		3.6	25	
		IF = 10 mA; f = 100 MHz; note 1		1.5	5	
charge carrier life time	τ L	when switched from IF = 10 mA to IR = 6 mA; RL = 100 Ω ;measured at IR = 3 mA		550		ns

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

■ Marking

Marking	A5
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